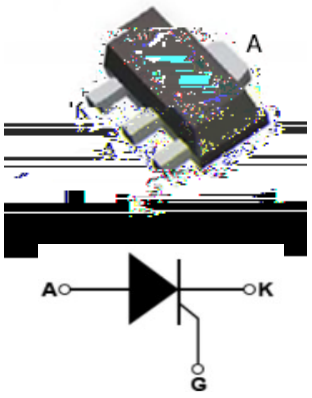
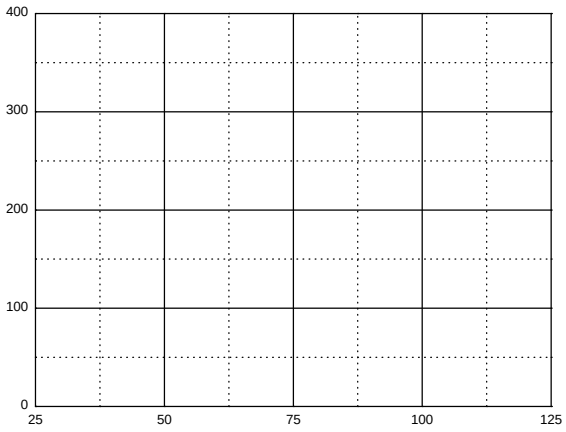
- Current-I_{GT} : 200 μA
  I_{TRMS} : 0.8 A
- V_{RRM}/ V_{DRM} : MCR100-6: 400 V
  MCR100-8: 600 V
- Operating and storage junction temperature range
- T_J T_{stg} : -55 to +150

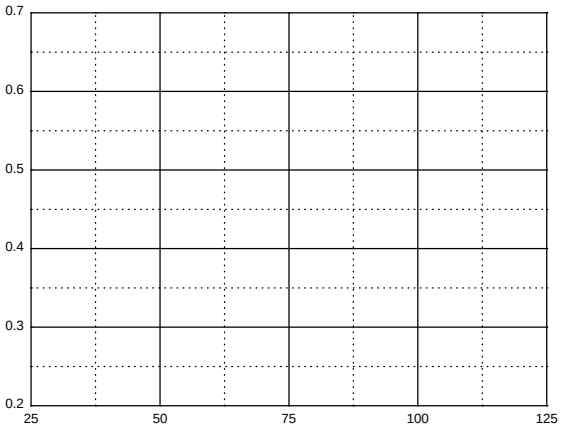


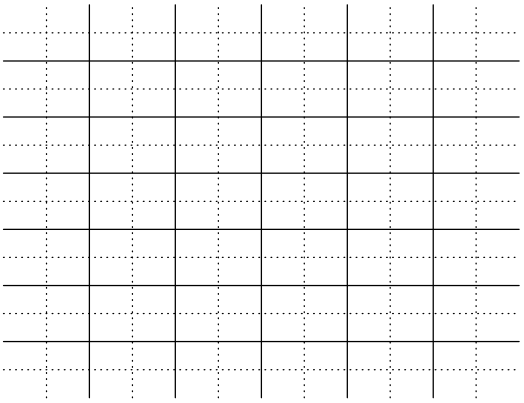
SOT-89

Parameter	Symbol		Test conditions	Min	Max	Unit
On state voltage	V_{TM}*		I_{TM}=1A		1.7	V
Gate trigger voltage	V_{GT}		V_{AK}=7V		0.8	V
Peak Repetitive forward and reverse blocking voltage **MCR100-6** **MCR100-8**	V_{DRM} AND V_{RRM}		I_{DRM}= 10 μA	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}		V_{AK}= Rated V_{DRM} or V_{RRM}		10	μA
Holding current	I_H		I_{HL}= 20mA ,V_{AK} = 7V		5	mA
Gate trigger current	I_{GT}	A2	V_{AK}=7V	5	15	μA
		A1		15	30	μA
		A		30	80	μA
		B		80	200	μA

* Forward current applied for 1 ms maximum duration duty cycle ≤ 1%


400
300
200
100
0
25
50
75
100
125


0.7
0.6
0.5
0.4
0.3
0.2
25
50
75
100
125



	Tape/Reel,7”reel	1000pcs/Reel	6000PCS/Box 30000PCS/Carton cse/Rc

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